

HIGH SPEED HRC FUSE LINK
POWER SEMICONDUCTOR
PROTECTION
250 V ~ 5 to 700 AMPS

250 V \sim 5 to 700 AMPS 600 V \sim 5 to 500 AMPS 1000 V \sim up to 1000 AMPS



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INTRODUCTION

Power Semiconductors are associated with HRC fuse links (fast acting type) for their protection, due to their smaller thermal withstand capacity. These fast acting fuses allow a smaller l²t letthrough during fault conditions, and thereby protect the Semiconductor. The operation of these fuse links, is affected by the higher ambient temperature (because of the smaller space available in the semiconductor circuit panel for the dissipation of heat to the surrounding) and severe load duty cycle. The various types of fuses available for semiconductor protection and the fuse performance figures and the characteristic curves are described in detail in this brochure. A few examples are also given, on the method of selection of the fuse links.

PARAMETERS OF POWER SEMICONDUCTOR FROM THE PERFORMANCE POINT OF VIEW

Power Semiconductors such as rectifiers and thyristors are widely used in electrical traction, large power supply unit and in the motor drive circuits in Textile Industries, Cement Mills and Paper Mills. The prospective fault current in such installation is very high and the costly semiconductors are liable to get damaged on the occurrence of a fault. Due to the smaller thermal withstand capacity of these devices (because of their smaller size) the energy let through by the protecting equipment in series with it, must be much lower than the device itself. The failure of the Semiconductor could be due to one of the following reasons:

- Very high I²t value let through by the fuse.
- b. Very high current peak produced by the fuse.
- Very high amount of reverse voltage developed by the fuse.
- d. Low values of overload current for a long time.

To prevent this failure, fast acting type HRC fuse links are developed which have low I2t, cut-off current and arc voltage compared to the device value.

All the manufacturers of Power Semiconductors specify the limiting values of the above parameters for their device. As the temperature produced by these devices during operations is very high (of the order of 150°C) the connected equipments, especially the rating of the protecting fuse must be properly selected as it is temperature-sensitive. From the four main parameters mentioned, it can be seen how they are useful in deciding the fuse rating for protection, in the next chapter.

FUSE LINK FOR SEMICONDUCTOR PROTECTION

General purpose HRC fuse links are not normally used for Power Semiconductor protection as they do not give adequate protection, because of their higher energy let through. An improved and specially designed version of the former type is fast acting HRC fuse links, which are being used with power semiconductors.

For power semiconductor protection, two types of fuses are available. One is fast acting HRC fuse link, the other is ultra fast acting fuse link. The former type is used for "internal protection" in high power equipments. Here, the fuse usually eliminates an overcurrent fault, following the failure of a semiconductor. The purpose of the fuse is to disconnect the faulty Semiconductor and protect the other devices,

The latter type, i.e. ultra fast acting fuses act very fast with minimum energy let through. These are used for "total protection", basically, to protect the Semiconductors when subjected to overload fault.

The fuses have been designed and tested to international specifications. The actual service conditions differ far from the designed conditions. As an example, the load that will be connected to the fuse may be cyclic overload or variable load as in the case of motor drive circuits. The fuses have also been tested for pulse withstand capabilities and overloads. The normal tests were carried out at a room temperature, of 25°C to 30°C. For higher ambient temperature application, (the temperature inside the panel of high power rectifier drive circuits may be of the order of 50 to 55°C), proper correction factors are taken into account to fix the rating.



The following characteristic curves define the fuse behaviour. Basically there are two ranges of fuses in English type i.e. 250 volt and 600 volt range. For higher current requirement double body fuses are suitable, which give low cut-off and I²t values.

1. Time - current characteristics

It helps in finding out the time required for clearing a particular overload fault.

2. Operating I2t characteristics

This gives the variation of energy let through by the fuse with different prospective fault current. This graph is useful when comparing the l2t value with that of the semiconductor device value.

3. Cut-off current characteristics

The peak value of the current let through by the fuse is obtained from this graph for any particular prospective current. This value must be smaller than the IFSM value of the semiconductor device.

4. Arc Voltage Characteristics

The relationship between the peak arc voltage generated by the fuse at various applied voltage is given here. This is compared with the devices, peak inverse voltage.

5. Variation of I2t with Applied Voltage

As the I²t is a function of the voltage, a relationship between the applied voltage and I²t value at these points is given here. The fuse value will be compared with the device I²t withstand.

6. Pre-Arcing I2t

This value is given in Annexure II for all the rating of fuses. This data is useful when comparing the operation of the fuses of different rating in a circuit.

SELECTION AND CO-ORDINATION OF FUSE LINK WITH THE SEMICONDUCTOR DEVICE

The steps for selecting the fuse link are listed below:

- Note down the semiconductor device information such as IFSM, I²t. VRSM etc.
- Type of the circuit in which the device is used. From the Annexure I, corresponding to the circuit, note down the various values.
- Choose a fuse link whose voltage and current rating are slightly higher than the semiconductor value.
- Calculate the prospective short-circuit current expected to flow in the circuit, knowing the
 percentage impedance of the source.
- With the above prospective current, obtain the l²t let-through by the fuse, from the l²t characteristics of the fuse. This must be smaller than the device withstand value.
- Obtain the peak value of the let through current by the fuse from the fuse cut off current characteristics. This value must be lesser than the Transient current withstand value (IFSM) of the device.
- Note down the arc-voltage developed by the fuse from the Arc-voltage characteristics, knowing the voltage at which the device operates. This value must be less than the Nonrepetitive peak reverse voltage (VRSM) of the device.
- The fuse rating selected thus, to conditions 5, 6 and 7 will protect the device. If there is any
 deviation from the conditions, select the next nearest rating. As the ambient temperature
 and load duty cycle play a vital role in the selection of the fuse, consult Works for the
 correct selection.

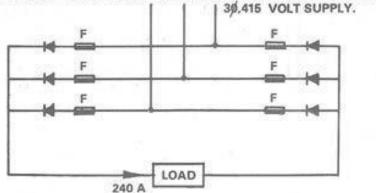


Type Reference	Rated Voltage (in Volts)	Current rating (in Amps)	Power loss (in Watts)	Maximum Breaking capacity (kA rms)
SFA (SINGLE BODY)	240 240 240 240 240	5 10 15 20	1.4 2.0 3.2 4.0	100
SFC (SINGLE BODY)	300 300 300 300 300 300 300 300	25 50 75 100 125 150 175	4.2 5.0 9.0 9.0 10.5 14.0 17.5	100
SFE 3 (SINGLE BODY)	300 300 300 300 300 300 300	125 150 200 250 300 350	14.0 16.0 20.0 25.0 29.0 33.0	100
SFG3 (DOUBLE BODY)	300 300 300 300	400 500 600 700	36.0 42.0 50.0 58.0	100
SFB (SINGLE BODY)	600 600 600 600	5 10 15 20	2.0 3.0 4.0 5.0	100
SFD (SINGLE BODY)	600 600 600 600	25 45 50 75	5.5 8.5 10.0 11.5	100
SFF (SINGLE BODY)	600 600 600 600	100 150 200 250	9.0 15.0 20.0 25.0	100
SFJ (SINGLE BODY)	600 600 600 600 600 600	16 25 30 35 40 50	4.3 5.5 6.2 7.5 8.0 10	100
SFJ (TWIN BODY)	600 600 600 600	75 85 110 150	13.0 13.5 16.0 20.0	100
SFH (DOUBLE BODY)	600 600 600 600 600 600 600 600 600	175 200 235 275 300 325 350 400 450 500	20.0 21.5 23.0 25.0 30.0 33.0 37.0 40.0 46.0 50.0	100



EXAMPLES

1 PROTECTION OF THREE PHASE FULLY CONTROLLED BRIDGE CIRCUIT.



1.1. Circuit Information:

Input voltage

: 415 Volts AC, 3 phase

F: FUSE

Percentage Impedance of

transformer

: 6%

DC output current

: 240 Amps

1.2. Device Information

One thyristor is connected per arm.

I2t withstand value: 30 x 103 Amp. sq.sec.

(IFSM) Max. non repetitive

2400 Amps

forward surge current : (VRSM). Max. non repetitive

1200 Volt

peak reverse voltage ;

Procedure for selection of fuselink
 From the load diagram, we have the following relationships.

lac1 = 0.816 ie lac1 = 195 Amps

ldc

lacz = 0.577 ie lacz = 138 Amps

1.3.1 The Maximum short circuit current that is likely to flow during fault conditions

$$= 195 \times \frac{100}{6}$$

= 3250 Amps

- 1.3.2. Choose a fuse link of rating, nearly equivalent to the line current (or the device nominal rating) which it is going to carry. So we get SFH/200 as the nearest/rating.
- 1.3.3. From the characteristics of SFH/200, we get I²t let-through, cut-off and peak arc voltage at 415 volts and prospective fault current of 3250 Amps.
 I²t let-through = 16.8 x 10³. This is much smaller than the device I²t withstand

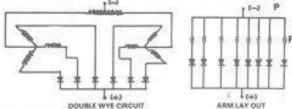
capacity.

- 1.3.4. Cut-off current = 2.7 KA. This is also much smaller than the device peak withstand current (ie 4800 Amps assuming a factor of 2)
- 1.3.5. Peak arc voltage = 615 volt. This value is also very much lower compared to the device Non repetitive peak reverse voltage.
- 1.4. From the above steps it is found that SFH/200 is the right choice for the above circuit.



PROTECTION OF POWER RECTIFIER CIRCUIT.

The diagram of the circuit is shown below:



2.1 Circuit Information:

Three phase double wye rectifier connection.

AC voltage (line to Jine): 185 Volt.

Transformer percentage inpedance: 8%

DC output current: 8000 Amps

8 diodes per arm. One fuse in series with each diode.

2.2 Device Information

Continuous current rating of the semiconductor: 350 Amps
I²t withstand capacity of the semiconductor: 240 x 10³ Amp, sq. sec.
Maximum Non repetitive forward surge current (IFSM): 6230 Amps
Maximum Non repetitive peak reverse voltage (VRSM): 1200 Volts

2.3 Analysis of the circuit.

2.3.1 Knowing the circuit arrangement we have the following relationships from Annexure I. The rms value of line current = 8000 x 0.289 = 2312 Amps

The magnitude of the arm current = 2312 Amps

2.3.2 From the transformer percentage impedance the maximum fault current is given by:

$$= 2312 \times \frac{100}{8}$$

= 28,900 Amps

2.3.4 In order to get the required arm current of 2312 Amps a number of diodes are connected in parallel, (ie 8 diodes are in parallel)

In the event of failure of one path, the actual current through the other paths

=
$$\frac{2312}{7}$$
 = 330 Amps
Expected short circuit fault current = $\frac{28,900}{7}$ \circlearrowleft 4130 Amps

2.3.6 The cut-off current value is 5 kA. This is also lesser than the peak withstand current of the device.

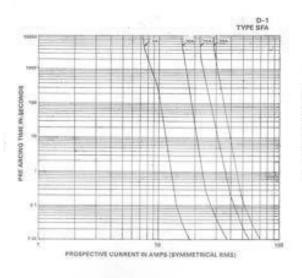


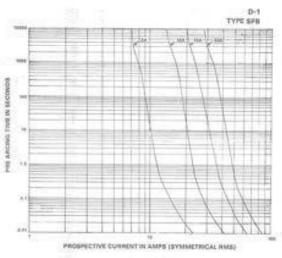
	TYPE	RATING AMPS	Α	В	С	D	Ε	F	G	н	J	K
	SFA	5 to 20	28 ± 1.0	8.2	-	46 ± 1.0	6.4	0.8	38 ± 0.5	4	4.8	8.8
SINGLE BODY	SFB	5 to 20	54 ± 1.0	8.2	-	74 + 1.0	6.4	0.8	64.3 ±0.5	4	4.8	8.8
D	SFC & SIFC	25 to 175	29 ± 1.0	17.5	128	58 ± 1.0	12.6	2	41.8 ± 0.5	6.4	8	19
-JI- FLAN P.B-1	SFD & SIFD	25 to 75	50 +1.0	17.5	=	78.5 ± 1.0	12.6	2	63.5 ±0.5	6.4	8	19
ELEVATION END VIEW	SFE3 & SIFE3	150, 200 250, 300 350	31.5 +1.0	38.5	1	84 ±1.0	25.4	3.2	59 <u>+</u> 1.0	10.3	13	41.
22	SFF & SIFF	100, 150 200,250	59 ±1.0	38.5	-	113 ±1.0	25.4	3,2	83 ±1.0	10.3	13	41.
	SFJ & SIFJ	15 to 55	50 ±1.0	17.5	1	78 + 1.0	12.6	2	63 ± 1.0	6.4	8	19
DOUBLE BODY	SFG3 & SIFG3	400 500 600 700	32.5 ± 1.0	38,5	-	84 +1.0	25.4	6,4	59 ± 1.0	10.3	13	88 +1.
PLAN END VIEW	SFH & SIFH	175 200 225 235 275 300 325 360 400 450 500	59 +1.0	38.5	-	113 +1.0	25.4	6.4	83 + 1.0	10.3	13	88 + 1.
PLAN SIDE VIEW	3FJ 8 SIFJ	75 To 150	47 +1.0	36	-	94 ±1.0	32	1.6	70 ± 0.5	B.7	10.3	19
Spring fooded indicator released when fuse operates for operating auxiliar/sequipment	SF 400 SF 500	300 V	47 + 1.0	0.8	6.4	5.6	19	5.6	7.9		_	2

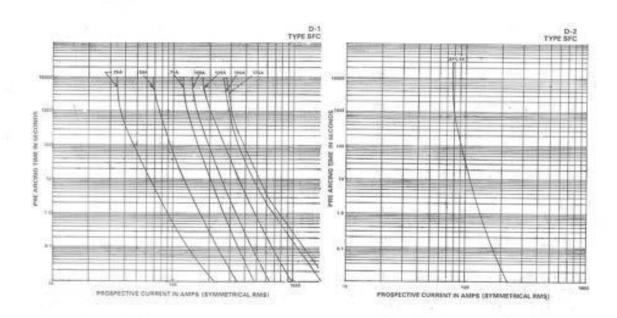
SIFC, SIFD, SIFE3, SIFF, SIFG3 SIFH and SIFJ are with indicator.



TIME CURRENT CHARACTERISTICS

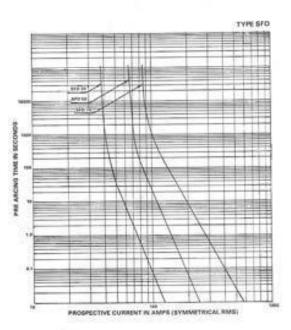


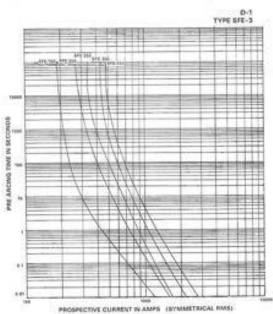


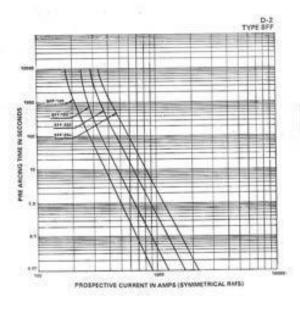


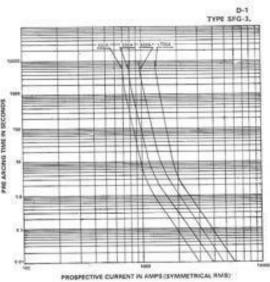


TIME CURRENT CHARACTERISTICS



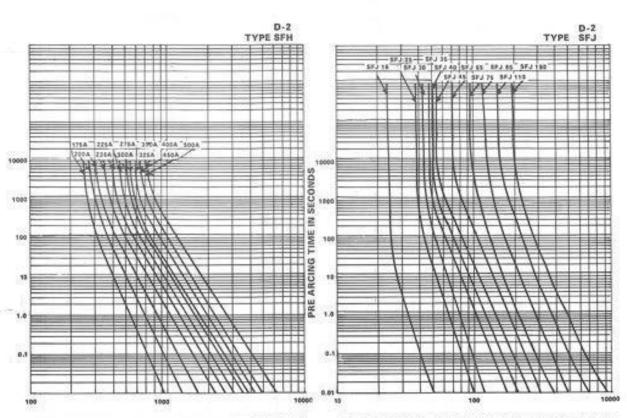








TIME CURRENT CHARACTERISTICS

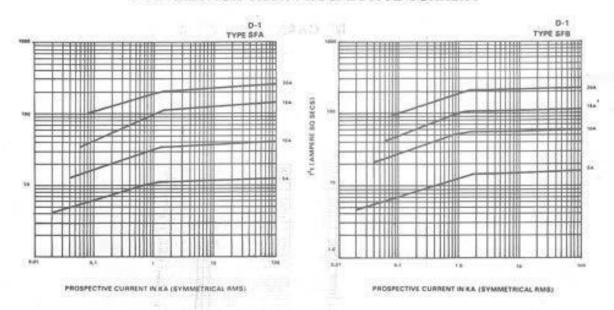


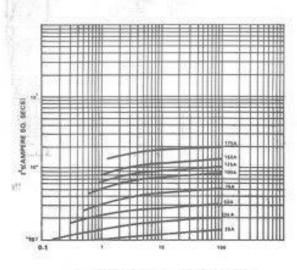
PROSPECTIVE CURRENT IN AMPS (SYMMETRICAL RMS)

PROSPECTIVE CURRENT IN AMPS (SYMMETRICAL RMS)



I2 t VARIATION WITH PROSPECTIVE CURRENT

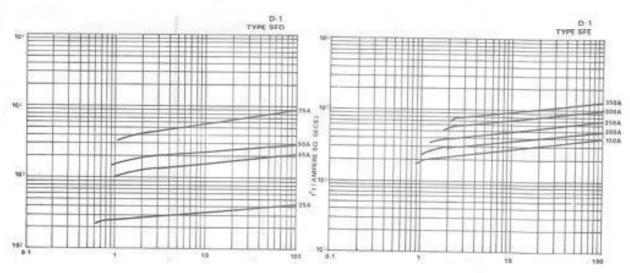




PROSPECTIVE CURRENT IN KA. (SYMMETRICAL RMS)

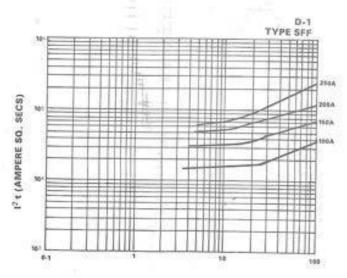


I2 t VARIATION WITH PROSPECTIVE CURRENT



PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

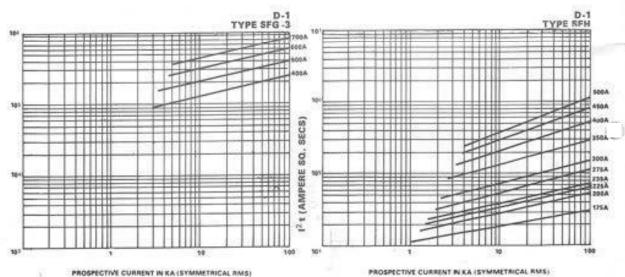
PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)



PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

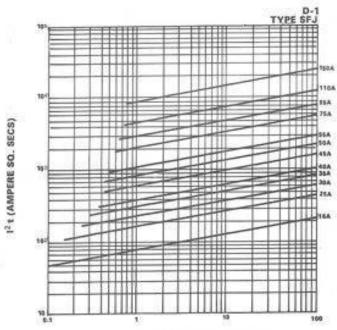


12 t VARIATION WITH PROSPECTIVE CURRENT





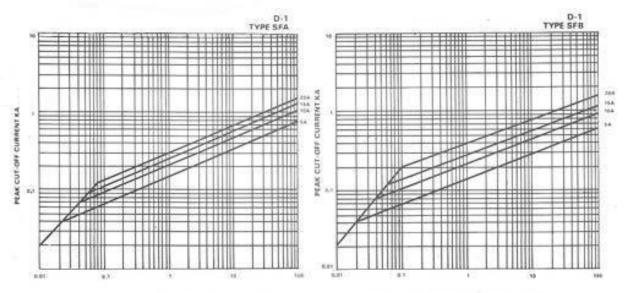
PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)



PROSPECTIVE CURRENT IN KA. (SYMMETRICAL RMS).

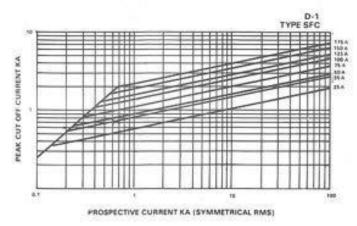


CUT OFF CURRENT CHARACTERISTICS



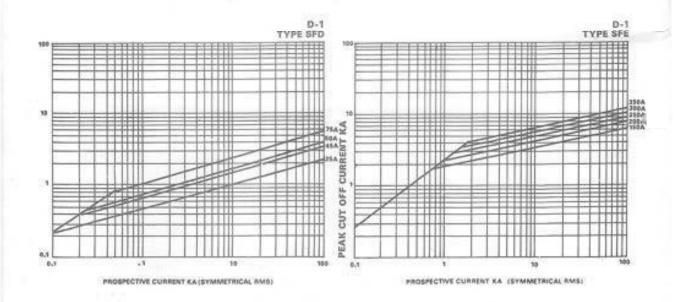
PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

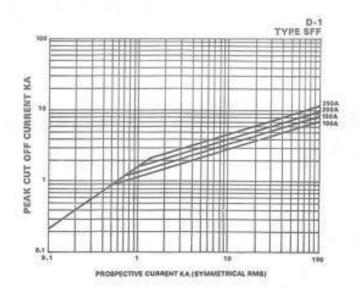
PROSPECTIVE CURRENT KA (SYMMETRICAL RMS)





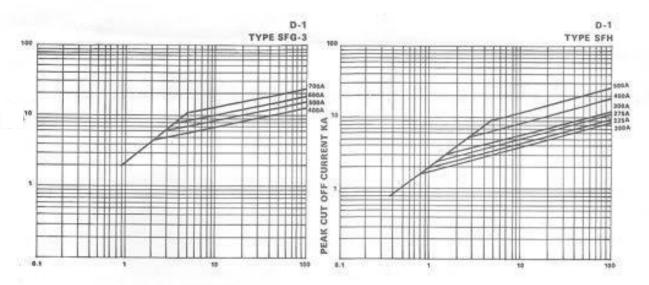
CUT OFF CURRENT CHARACTERISTICS





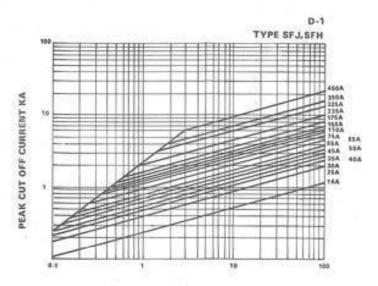


CUT OFF CURRENT CHARACTERISTICS



PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

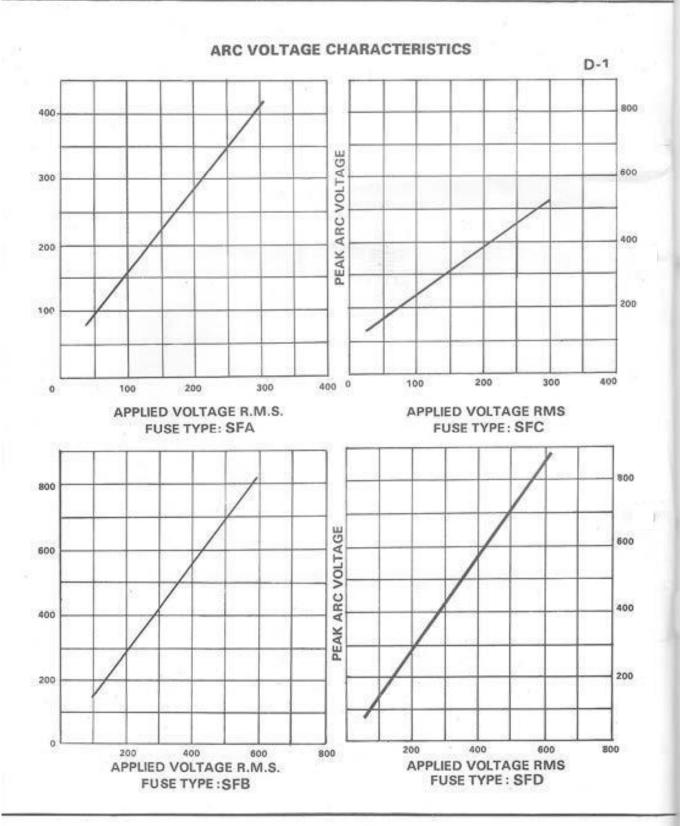


PROSPECTIVE CURRENT IN KA (SYMMETRICAL RMS)

NOTE

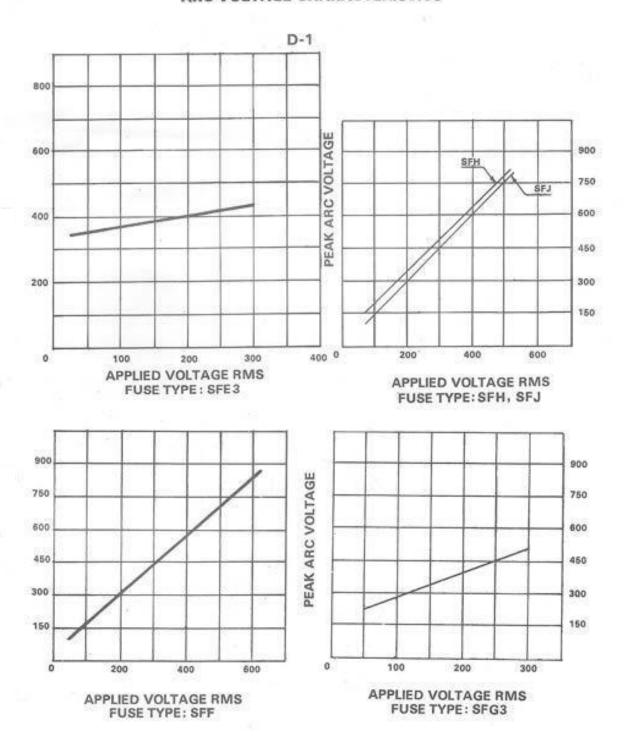
SFJ-16A TO 150A SFH-175A TO 500A







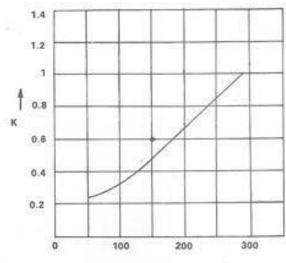
ARC VOLTAGE CHARACTERISTICS



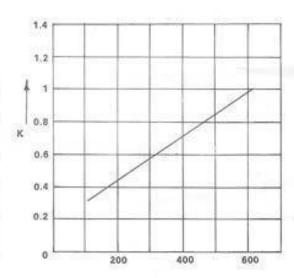
19



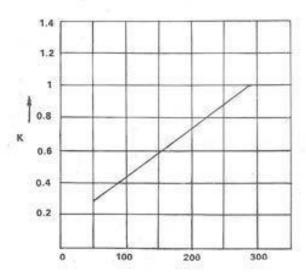
MULTIPLICATION FACTOR (K) FOR I2t VALUE AT DIFFERENT VOLTAGE



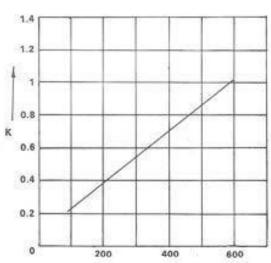
APPLIED VOLTAGE (RMS) FUSE TYPE: SFC



APPLIED VOLTAGE (RMS) FUSE TYPE: SFD



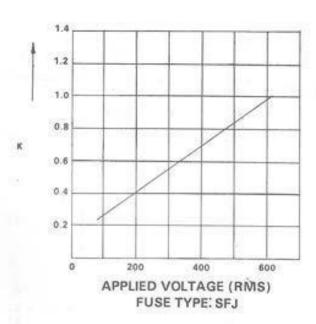
APPLIED VOLTAGE (RMS) FUSE TYPE: SFE

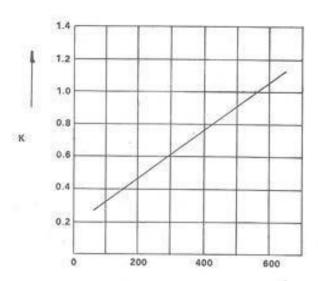


APPLIED VOLTAGE (RMS) FUSE TYPE: SFF



MULTIPLICATION FACTOR (K) FOR 12t VALUE AT DIFFERENT VOLTAGE





APPLIED VOLTAGE (RMS) FUSE TYPE: SFH



Fuse Type reference	Current rating (amps)	Prearcing I ² t	Fuse Type reference	Current rating (amps)	Prearcing I ² t
SFA	5 10 15 20	1.5 5.0 10.5 26.0	SFD	25 45 50 75	51 110 185 520
SFC	25 50 75 100 125 150 175	140 250 540 700 1150 2600 5040	SFJ	16 25 30 35 40 45 50	13 25 42 58 84 110 180
SFE 3	150 200 250 300 350	3300 7500 11,300 14,670 18,600		55 75 85 110 150	260 480 600 770 1850
SFG 3	400 500 600 700	18,000 36,000 42,000 70,000	SFH	175 200 225 235 275	1600 2500 2800 3700 5100
SFB	5 10 15 20	1.8 6.0 13.0 30.0	5FH	300 350 400 450 500	6900 11,000 14,400 33,000 54,000



ANNEXURE I

VARIOUS CIRCUIT ARRANGEMENT AND THE RELATIONSHIP BETWEEN DIFFERENT PARAMETERS

OF THE CIRCUIT	Vac Vdc	lav Ide	lac ₁ ldc	lac ₂	Vr Vdc	Vr Vac	NAME OF THE CIRCUIT
1 (4000)	2.22	1.0	1.57	1.57	3.14	1.41	SINGLE PHASE HALF-WAVE RECTIFIER
	2.22	0.5	0.707	0.707	3.14	2.82	SINGLE PHASE FULL-WAVE RECTIFIER
	1.11	0.5	0,707	1.00	1.57	1.41	SINGLE PHASE BRIDGE CIRCUIT
	1.48	0.33	0.577	0.577	2.09	2.45	THREE PHASE WYE CONNECTION
	2.22	0.167	0.236	0.236	3.14	2.83	THREE PHASE TRIPLE DIAMETRIC
	0.74	0.333	0.577	0.816	1.05	2.45	THREE PHASE BRIDGE CIRCUIT
	1.48	0.167	0.289	0.289	2.00	2.45	THREE PHASE DOUBLE WYE CIRCUIT
(a)	1.48	0.167	0.408	0.408	1.05	2.83	SIX PHASE STAR CONNECTION
(1) (1) (1) (1) (1) (1) (1) (1) (1) (1)	0.715	0.167	0.408	0.577	1.05	2.83	SIX PHASE PARALLEL BRIDGE (WITHOUT INTER PHASE TRANSFORMER)
Pipe 1544	0.74	0.167	0.289	. 0.408	1.05	2.83	SIX PHASE PARALLEL BRIDGE (WITH INTER PHASE TRANSFORMER)
	0.37	0.334	0.578	0.816	1.05	2.45	SIX PHASE SERIES BRIDGE

Details of Notation used

Vac Vdc

No load r.m.s ac Voltage (line) No load d. c. Voltage

Average value of rectified current per arm

lac1 lac2 ldc Vr

Arm Current Value in r.m.s. Line Current Value in r.m.s. DC Output current Reverse voltage across the rectifier

Our Other Products

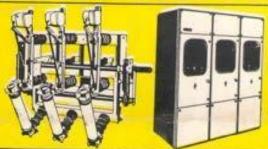


General Purpose Fuse Link from 2 Amp to 630 Amp in bolted type and knife blade type tag version Tested to 92 kA short circuit level.



Potential Transformer fuses upto 36 kV and 3 Amps.

High Voltage Isolators (indoor/outdoor type) upto 36 kV



High Voltage Load Break Switches (indoor/outdoor type) upto 36 kV and 630 Amp

Due to continuous development, data given are likely to change.

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